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Large two-level magnetoresistance effect in doped manganite grain boundary junctions

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We performed a systematic analysis of the tunneling magnetoresistance (TMR) effect in single grain boundary junctions formed in epitaxial $La_{2/3}Ca_{1/3}MnO_3$ films deposited on $SrTiO_3$ bicrystals. For magnetic fields H applied parallel to the grain boundary barrier, an ideal two-level resistance switching behavior with sharp transitions is observed with a TMR effect of up to 300% at 4.2 K and still above 100% at 77 K. Varying the angle between H and the grain boundary results in differently shaped resistance vs H curves. The observed behavior is explained within a model of magnetic domain pinning at the grain boundary interface.

Ferromagnetic tunneling junctions have been studied intensively over the last years due to possible applications in magnetoelectronics devices. The tunneling magnetoresistance (TMR) between two ferromagnetic layers $i = 1, 2$ separated by a thin insulating barrier depends on the relative orientation of the magnetization and the spin polarization $P_i = 2a_i - 1$, where a_i is the fraction of majority spin electrons in the density of states of layer i. Within the Jullière model[1], the TMR is estimated to

$$\frac{\Delta R}{R} = \frac{R_{\uparrow\downarrow} - R_{\uparrow\uparrow}}{R_{\uparrow\uparrow}} = \frac{2P_1P_2}{1 - P_1P_2} , \qquad (1)$$

where $R_{\uparrow\uparrow}$ and $R_{\uparrow\downarrow}$ is the tunneling resistance for parallel and anti-parallel magnetization orientation. Depending on the spin polarization, for parallel magnetization the tunneling resistance is significantly reduced, since the large density of occupied and empty states for the majority spin electrons in both junction electrodes allow for a large tunneling current. We note that in the Jullière model only elastic tunneling without any spin-flip processes is assumed and the junction electrodes are assumed to be single domain.

So far, most of the investigated TMR devices are based on transition metals and compounds such as Ni, Co, Fe, or $Co_{50}Fe_{50}$ with $P \lesssim 50\%$ (for recent overviews see Moodera *et al.*[2] and Parkin *et al.*[3]). It is evident that P close to unity is desired to achieve a high TMR-effect. There are several candidates for materials with large P close to 100% such as the Mn-based Heusler alloys[4], the oxide ferromagnets as Fe_3O_4 or CrO_2, and the doped manganites of composition $La_xD_{1-x}MnO_3$ with $D =$ Ca, Sr, and Ba. While for the former materials the high spin polarization is still under question[5], recently photoemission spectroscopy has provided direct evidence for the half-metallic nature of $La_{0.7}Sr_{0.3}MnO_3$[6] with P close to unity. Indeed, using doped manganites high TMR values have been achieved[7,8], including trilayer spin valve devices with a TMR value above 450% at 4.2 K corresponding to a spin polarization above 80%[9,10] and even above 1000% at 4.2 K corresponding to a spin polarization above 90%[11]. We emphasize that the TMR-effect in manganite tunnel junctions is observed at low applied magnetic field of less than 100 mT and has to be distinguished from the intrinsic, high-field colossal magnetoresistance (CMR) of the doped manganites[12,13]. While most tunnel junctions rely on multilayer technology, one can also form ferromagnetic tunnel junctions by using well-defined individual grain boundaries (GBs) separating two ferromagnetic grains. This is achieved by growing epitaxial manganite films on a $SrTiO_3$ bicrystal substrates[14,15,16,17,18]. In this configuration the barrier is formed by a straight, few nm wide distorted GB interface as shown by transmission electron microscopy[17,19,20]. After annealing in oxygen atmosphere, single GB junctions (GBJs) with large TMR effects have been achieved[14,15,16,17,18].

For many applications not only a large TMR effect but also a sharp switching between two distinct resistance values at a well-defined magnetic field is required. Such ideal, almost rectangular shaped $R(H)$-curves with a maximum resistance change below 50%[7] have been observed for some devices based on transition metals. However, for tunnel junctions based on doped manganite junctions (and also for many devices based on transition metals), usually strongly rounded and noisy $R(H)$ curves[8], sharply peaked structures[14], or multiple resistance level switching is reported. This behavior most likely originates from an uncontrolled domain switching. Here, we present a detailed study of the shape of the $R(H)$ curves of GBJs based on doped manganites. We show that an almost perfect two-level resistance switching behavior with a sharp transition between the resistance values can be obtained. We further show that such ideal behavior is achieved with the magnetic field applied within the film plane parallel to the GB barrier. We also demonstrate that it is possible to vary the magnitude of the switching field H_s by changing the angle between the GB and the applied field. Our results provide evidence that domain wall pinning structures, intergrain coupling, and the direction of the applied field can be combined to taylor the $R(H)$-curves of magnetic tunnel junctions.

GBJs were fabricated by pulsed laser deposition of epitaxial, 80 nm thick $La_{2/3}Ca_{1/3}MnO_3$ films on symmetrical, [001] tilt $SrTiO_3$ bicrystals with a misorientation angle of 24°. After film deposition the samples were annealed ex-situ at 950°C in oxygen atmosphere for one hour. X-ray analysis of the films shows only (00ℓ) reflexes and the FWHM of the (002) rocking curve was 0.04°. Microbridges of $30\,\mu$m width straddling the GB were patterned using optical lithography and Ar ion beam etching. In this way, well-defined individual GBJs were obtained. The $\mathrm{La_{2/3}Ca_{1/3}MnO_3}$ films typically had a Curie-temperature T_C of about 225 K. Further details on the transport properties and the microstructure of the GBJs have been reported recently[16,17,18,19,20,21].

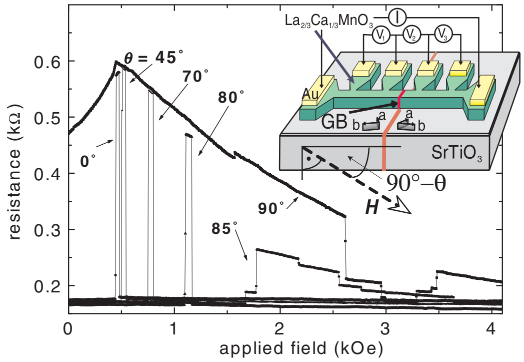

FIG. 1: $R(H)$ curves of a $\mathrm{La_{2/3}Ca_{1/3}MnO_3}$ GBJ for different angles θ between H and the GB barrier measured at 4.2 K and a bias voltage of 5 mV. For clarity, the $R(H)$ curve is shown only for one direction of the field sweep. The inset show a sketch of the GBJ geometry.

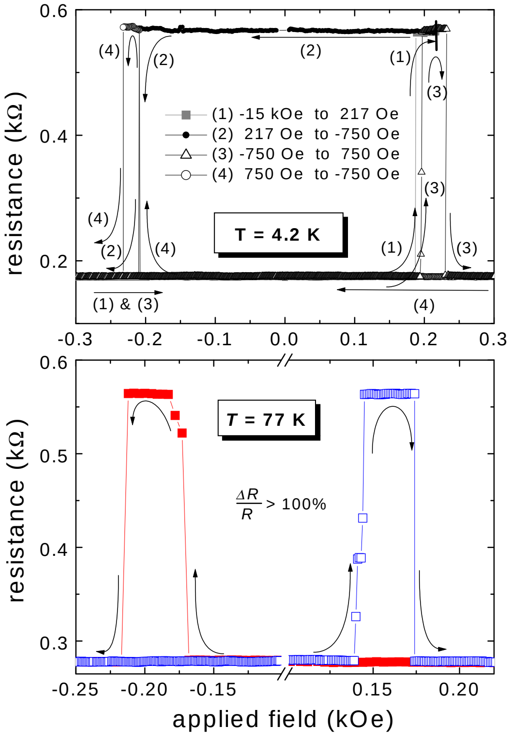

FIG. 2: $R(H)$-curves for $\theta = 0°$ at 4.2 K (upper panel) and 77 K (lower panel). The direction of the field sweep is indicated by the arrows.

In Fig. 1, typical $R(H)$ curves of a $\mathrm{La_{2/3}Ca_{1/3}MnO_3}$ GBJ are shown for different angles θ between the GB barrier and the magnetic field H, which always is applied within the film plane. For $0° < \theta < 80°$ rectangular shaped $R(H)$-curves are observed clearly indicating a two-level resistance switching behavior. Here, $\theta = 90°$ and 0° corresponds to $H \perp$ GB and $H \|$GB, respectively. The switching field H_s is shifted to larger values with increasing θ. At the same time the TMR effect decreases. For $\theta \gtrsim 80°$ several sharp jumps occur in $R(H)$ indicating a multi-level resistance scheme. At $\theta = 90°$, where $H \perp$ GB, a broad continuous $R(H)$ curve is observed forming the envelope of the $R(H)$ curves measured for $\theta < 90°$. In the $\theta = 90°$ curve still some jump-like resistance switches between well-defined states are observed. The field scale for H_s is set by the coercivity field H_c which varies for differently doped manganites. In addition, the measured switching field H_s depends on the velocity of the field sweep and the magnetic history indicating the importance of domain dynamics.

According to Jullière's model[1], a two-level behavior of the $R(H)$-curves is expected if the electrodes are considered to be single domain. The two resistance levels correspond to the fully parallel and anti-parallel magnetization configuration of the two ferromagnetic electrodes. That is, the $R(H)$-curves observed for $\theta = 0°$ are close to those expected according to the Jullière model for a tunnel junction consisting of electrodes with slightly different H_c. The $R(H)$ curves for $\theta = 0°$ are shown in more detail in Fig. 2 for several field sweeps. The switching between the two resistance levels occurs within less than 10 Oe at 4.2 K. When the direction of the field sweep is reversed on the high-resistance branch (curve 1), the junction stays in the high-resistance (opposite magnetization direction) state on crossing zero field (curve 2). That is, depending on the magnetic history two stable resistance values can be realized for $-H_s < H < H_s$. When the field is swept from a large negative to a large positive field value or vice versa (curves 3 and 4), the high-resistance state is reached after crossing zero field and has a plateau width of about 50-100 Oe. Increasing θ results in larger H_s and also larger plateau width.

From the measured value of $\Delta R/R \simeq 3$ at 4.2 K a spin polarization of $P_i \simeq 77\%$ is estimated. At 77 K the TMR effect is still above 100%, but the rectangular shape of the $R(H)$ curve starts to round. It still has to be clarified why the measured TMR values are below the Jullière value expected for an almost fully spin-polarized ferromagnet ($P_i \simeq 100\%$). Possible reasons are spin-flip processes arising from inelastic transport via localized states in imperfect tunneling barriers[16] or scattering from magnetic excitations[22]. Such effects are not included in the Jullière model. Furthermore, strain effects in the manganite films may be responsible for a reduced spin polarization close to the GB. Unfortunately, little is known on the detailed interface and surface properties of doped manganites. Nonetheless, the fact that $P \approx 80 - 90\%$

has already been observed[9,11] indicates that a further improvement of junction and interface quality will allow for a further increase of the TMR effect both in GBJs and planar tunnel junctions based on doped manganites.

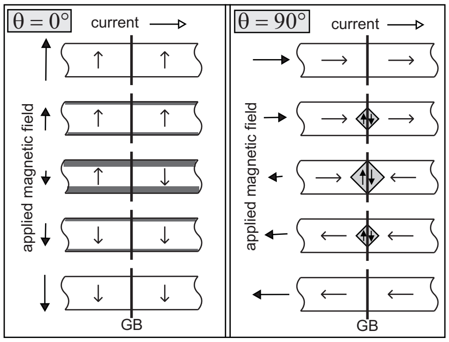

FIG. 3: Sketch of the domain structures in a manganite thin film sample containing a single GB for applied magnetic fields of different magnitude and direction. The shaded parts represent regions consisting of domains with perpendicular and non-collinear magnetization with respect to the applied field. In the left hand panel the width of the shaded parts is overemphasized.

We now discuss the dependence of the shape of the $R(H)$-curve on the direction of the applied field using a simple domain model taking into account the magnetic domain pinning at the GB interface. A sketch of the expected domain structure is shown in Fig. 3 for $H \perp$GB and $H \|$GB. We first note that at the GB interface the easy axis of magnetization is parallel to the GB. This is well known from surface studies of magnetic materials[23]. Furthermore, for $|H| \gg H_c$ the magnetization is parallel to H in both junction electrodes, that is, $R(H)$ is low. However, on decreasing the field from $|H| \gg H_c$ a different domain structure is expected for different field directions. We first discuss the case $\theta = 0°$, where $H \|$GB, i.e. parallel to the easy axis at the GB. In this case, $R(H)$ can be low or high depending on whether the magnetization direction in the electrodes is parallel or anti-parallel. Furthermore, on varying the field in the high- resp. low-resistance state, a small resistance change below 1% is observed due to the formation of small domains with different magnetization direction at the edges of the sample (shaded regions in Fig. 3). Since these domains are small, they do not contribute considerably to the transport behavior and magnetoresistance of the GBJ. In a first approximation, both junction electrodes can be considered single domain as assumed in the Jullière model. We note that for $H \|$GB the single domains are strongly pinned by the GB interface. Thus, on decreasing the field amplitude from $|H| \ll H_c$ a parallel magnetization orientation and hence low $R(H)$ is preserved until the coercivity field of opposite direction is reached. Then, at $|H| \simeq H_c$ the magnetization direction in one electrode switches resulting in an anti-parallel magnetization configuration and, thus, high resistance state. This anti-parallel magnetization configuration is stabilized in a finite field range around H_c due to a reduction of the magnetic energy by reducing stray fields. On further increasing the field also the second electrode switches resulting again in a parallel magnetization configuration and low resistance state.

For $\theta = 90°$, we have $H \perp$ GB, i.e. H perpendicular to the easy axis at the GB. When the field is decreased, domains form at the GB with magnetization parallel to the GB. Since these perpendicular and non-collinear (with respect to the applied field) oriented domains are located at the GB, they will strongly affect the transport properties and magnetoresistance. In this case, the electrode regions adjoining the GB can no longer be considered as single domain. The measured triangular shaped $R(H)$ curves can be attributed to a continuous change of the size of the non-collinear domains. Note that for $|H| \ll H_c$ the magnetization configuration at the GB is similar for $\theta = 0°$ and $\theta = 90°$ resulting in similar $R(H)$ values in agreement with our experiments. We further note that for $\theta = 90°$ the anti-parallel domain configuration is present along the whole GB, because the applied field has no component parallel to the GB. Such a component destabilizes the anti-parallel configuration and, in turn, causes a switching of the magnetization. This explains why the $R(H)$ curves for $\theta = 90°$ form is the envelope of the $R(H)$ curves measured for $\theta < 90°$.

For intermediate $0° < \theta < 90°$ the behavior can be understood qualitatively within the same picture. An increase of θ is found to increasing H_s. This is caused by the fact that the field component parallel to the GB which drives the switching transition decreases with increasing θ. At the same time the plateau width of the high-resistance state becomes wider since the reduced parallel field component also drives the second switching transition into the low-resistance state by overcoming the energy gain in the anti-parallel configuration due to reduction of stray fields. Fig. 1 clearly shows that only for $\theta > 45°$ a significant angle dependence is observed. This is caused by the strong tendency of the domains to align parallel to the easy axis along the GB. Certainly, the direct imaging of the domain structure in the vicinity of the GB would be helpful to verify our model.[24] In particular, the formation of multiple stable resistance states for large θ that may be related to the microstructure of individual GBs and their interface roughness has to be clarified. Similar effects have also been observed in planar sandwich junctions employing Co and MnFe electrodes with different aspect ratios[25]. So far, we have not studied in detail the influence of different GB misorientation angles. However, we suppose that the effect of different misorientation angles is small compared to the effect of the relative orientation between H and the GB discussed here.

In summary, we have shown that an almost ideal, two-level resistance switching behavior can be obtained for GBJs based on doped manganites. The switching field, the magnitude of the TMR effect, and the shape of the $R(H)$ curves can be varied systematically by varying the orientation of the applied field relative to the GB barrier. The measured $R(H)$ characteristics have been interpreted in terms of a simple domain model demonstrating the key role of a strong domain wall pinning at the grain boundary. Our results outline possible roads for the tayloring of the properties of magnetic tunnel junctions based on doped manganites for applications in magnetoelectronic devices.

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